

# 650 V Power SiC Gen 3 Merged PIN Schottky Diode, 20 A



#### **LINKS TO ADDITIONAL RESOURCES**





PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 20 A						
V <sub>R</sub>	650 V					
V <sub>F</sub> at I <sub>F</sub> at 150 °C	1.5 V					
T <sub>J</sub> max.	175 °C					
I <sub>R</sub> at V <sub>R</sub> at 175 °C	9 μΑ					
Q <sub>C</sub> (V <sub>R</sub> = 400 V)	53 nC					
Package	TO-220AC 2L					
Circuit configuration	Single					

#### **FEATURES**

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V<sub>F</sub> and efficiency by thin wafer technology



- Positive V<sub>F</sub> temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

#### **MECHANICAL DATA**

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		650	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 111 °C (DC)	20	Α		
DC blocking voltage	$V_{DC}$		650	V		
Repetitive peak forward current	I <sub>FRM</sub>	$T_C$ = 25 °C, f = 50 Hz, square wave, DC = 25 %	63	Α		
New venetitive needs forward over a coment	I <sub>FSM</sub>	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	110	A W		
Non-repetitive peak forward surge current		$T_C = 110$ °C, $t_p = 10$ ms, half sine wave	104			
Dawer dissination	P <sub>tot</sub> (1)	T <sub>C</sub> = 25 °C	93			
Power dissipation		T <sub>C</sub> = 110 °C	41			
I <sup>2</sup> t value	∫i <sup>2</sup> dt	T <sub>C</sub> = 25 °C	60.5	A <sup>2</sup> s		
	Jı-dt	T <sub>C</sub> = 110 °C	54	χ-5		
Operating junction and storage temperatures	T <sub>J</sub> <sup>(2)</sup> , T <sub>Stg</sub>		-55 to +175	°C		

#### Notes

<sup>(1)</sup> Based on maximum R<sub>th</sub>

<sup>(2)</sup> The heat generated must be less than the thermal conductivity from junction-to-ambient: dPp/dTJ < 1/ReJA



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I <sub>F</sub> = 20 A	-	1.3	1.5		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 20 A, T <sub>J</sub> = 150 °C	-	1.50	1.85	V	
		I <sub>F</sub> = 20 A, T <sub>J</sub> = 175 °C	-	1.60	-		
	I <sub>R</sub>	$V_R = V_R$ rated	-	1.3	100	μA	
Reverse leakage current		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 150 °C	-	5.5	250		
		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 175 °C	-	9	-		
Total capacitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	845		,,F	
		V <sub>R</sub> = 400 V, f = 1 MHz	-	82	-	pF	
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	53	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T <sub>A</sub> = 25 °C unless otherwise specified)							
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS							
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	1.2	1.6	°C/W	
Marking device	3C20ET07T						

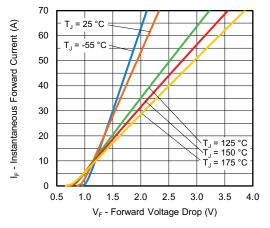


Fig. 1 - Typical Forward Voltage Drop Characteristics

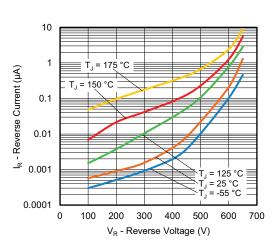


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

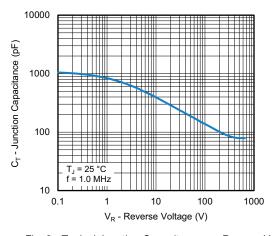


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

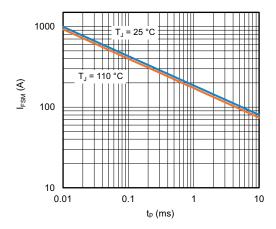


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

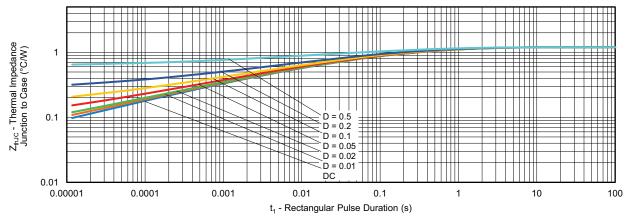


Fig. 5 - Typical Thermal Impedance  $Z_{thJC}$  Characteristics

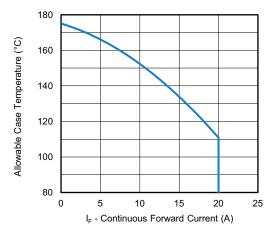


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

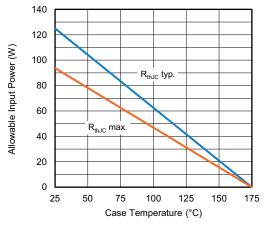


Fig. 7 - Forward Power Loss Characteristics

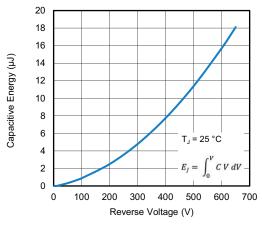


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

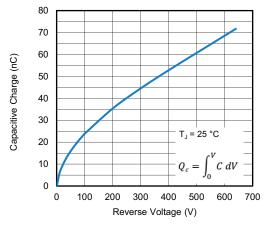
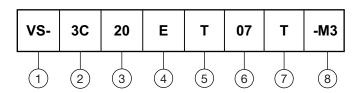


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

- 3C = SiC diode, Generation 3

Current rating (20 = 20 A)

- E = single diode

5 - Package TO-220

6 - Voltage rating: (07 = 650 V)

7 - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

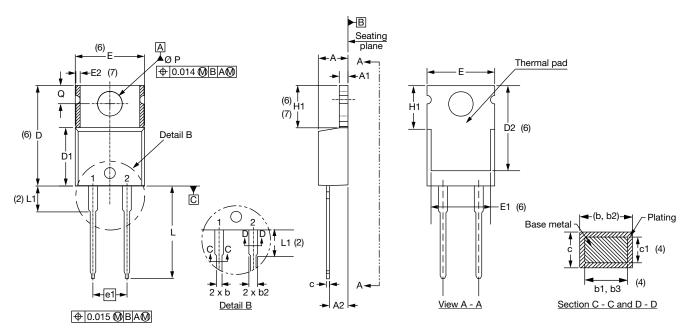
ORDERING INFORMATION						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-3C20ET07T-M3	50/tube	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96069</u>					
Part marking information	www.vishay.com/doc?95391				



## **TO-220AC 2L**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	MILLIMETERS		INCHES		
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
e1	4.88	5.28	0.192	0.208		
H1	5.84	6.86	0.230	0.270	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØP	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except D2, where JEDEC® minimum is 0.480"



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